

AMENDMENTS TO THE CLAIMS:

The following listing of claims will replace all prior versions and listings of claims in this divisional application.

LISTING OF CLAIMS:

Claims 1-5. (Cancelled)

Claim 6. (Currently Amended) A method for manufacturing a trench isolation on a silicon substrate, comprising:
forming a trench area for device isolation in the silicon substrate, wherein the trench has inner sidewalls;
forming an oxide layer on a surface of the silicon substrate that forms the inner sidewalls of the trench;
supplying healing elements to the silicon substrate to remove dangling bonds; and
filling the trench with a device isolation layer
~~The method for manufacturing a trench isolation on a silicon substrate as claimed in claim 1,~~ wherein supplying the healing elements comprises:
forming an ion implanting layer on the oxide layer;
implanting the healing elements in the ion implanting layer by an ion implantation; and
diffusing the ion implanted healing elements by means of a thermal annealing process.

7. The method for manufacturing a trench isolation on a silicon substrate as claimed in claim 6, wherein the ion implanting layer is a polysilicon layer.

Claims 8-31. (Cancelled)